

Product Summary

BV_{DSS}	$R_{DS(ON)}$	Package	I_D $T_A = +25^\circ\text{C}$
-50V	8Ω @ $V_{GS} = -5V$	X1-DFN1006-3	-310mA

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

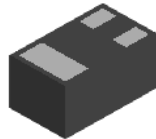
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected 1kV**
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

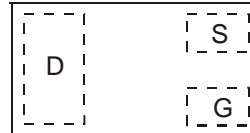
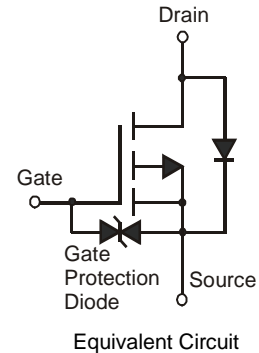
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu. Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.001 grams (Approximate)



X1-DFN1006-3



Bottom View



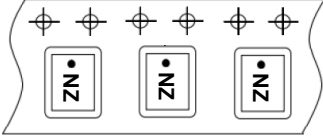
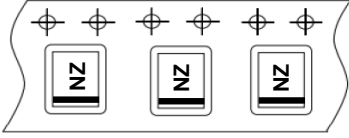

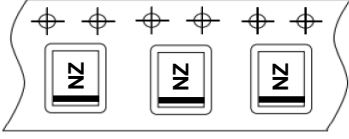

 Top View
Pin-Out


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP58D0LFB-7	X1-DFN1006-3	3,000 / Tape & Reel
DMP58D0LFB-7B	X1-DFN1006-3	10,000 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

DMP58D0LFB-7	<div style="display: flex; justify-content: space-around; align-items: flex-start;"> <div style="text-align: center;">  <p>Top View Dot Denotes Drain Side</p> </div> <div style="text-align: center;"> <p>From date code 1527 (YYWW), this changes to:</p>  <p>Top View Bar Denotes Gate and Source Side</p> </div> </div> <div style="display: flex; justify-content: space-around; align-items: center; margin-top: 10px;">   </div>
DMP58D0LFB-7B	<div style="text-align: center;">  <p>Top View Bar Denotes Gate and Source Side</p> </div> <div style="text-align: center; margin-top: 10px;">  </div> <div style="text-align: right; margin-top: 20px;"> <p>NZ = Part Marking Code</p> </div>

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-50	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = -5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-180 -150	mA
Continuous Drain Current (Note 6) V _{GS} = -5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-310 -250	mA
Pulsed Drain Current (Note 7)			I _{DM}	-500	mA

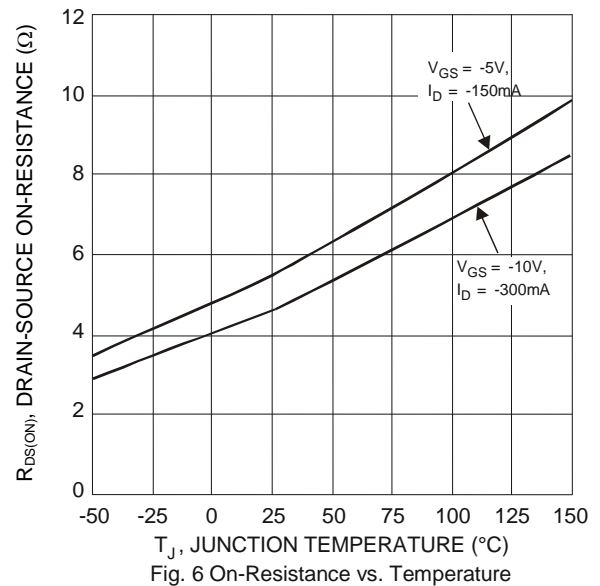
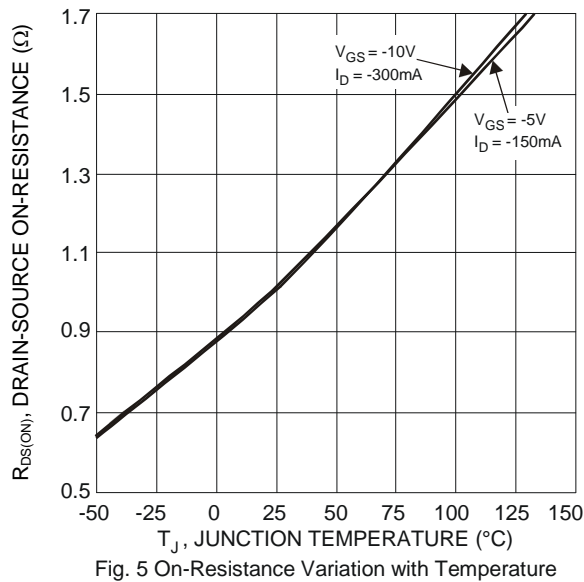
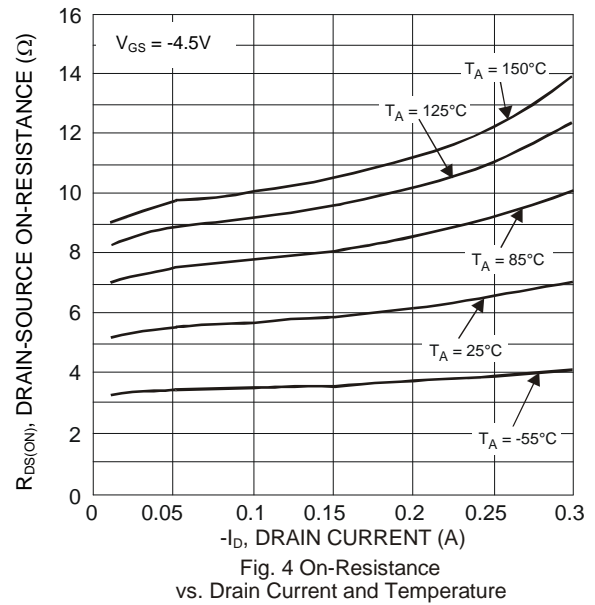
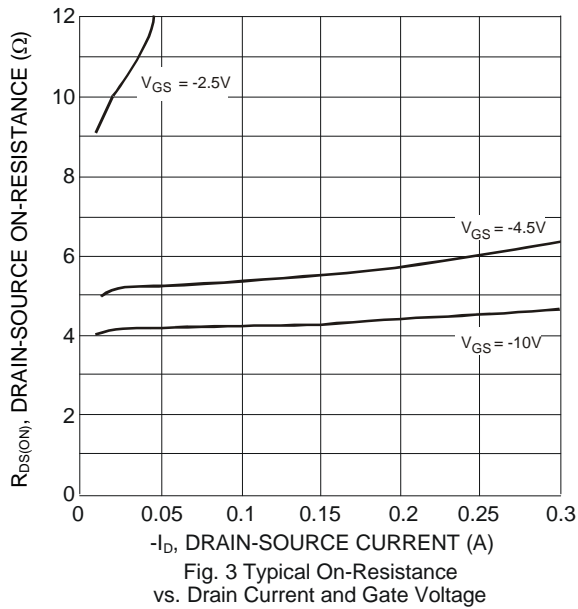
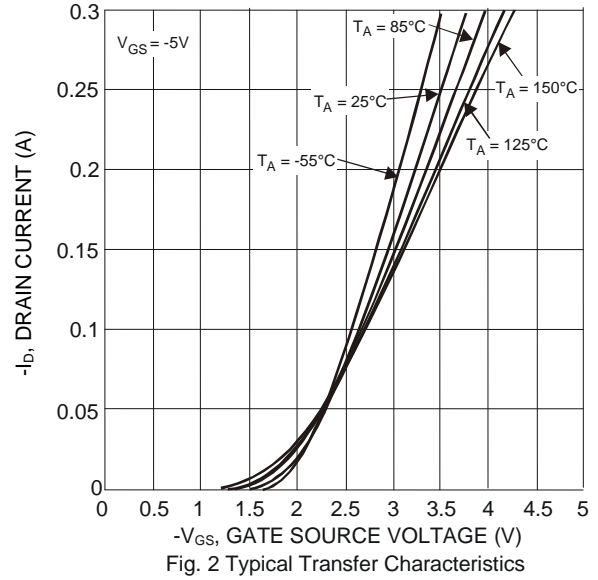
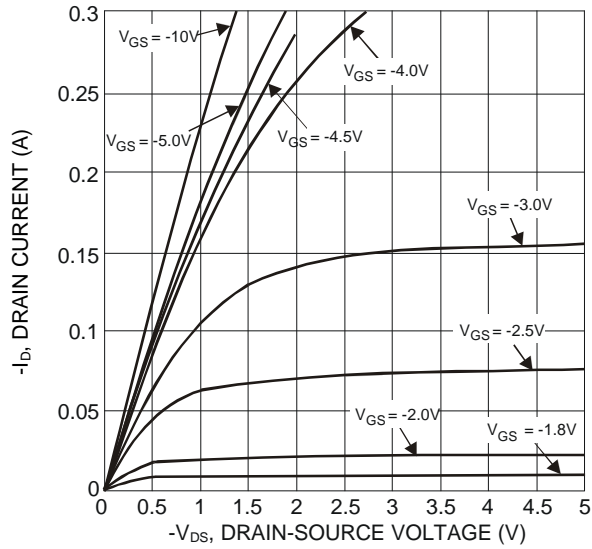
Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P _D	0.47	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	258	°C/W
Power Dissipation (Note 6)	P _D	1.22	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	105	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -50V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±5	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.8	—	-2.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6	8	Ω	V _{GS} = -5V, I _D = -100mA
		—	12	18	Ω	V _{GS} = -2.5V, I _D = -10mA
Forward Transfer Admittance	Y _{fs}	0.05	—	—	S	V _{DS} = -25V, I _D = -100mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	27	—	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	4.0	—		
Reverse Transfer Capacitance	C _{rss}	—	1.4	—		
Turn-On Delay Time	t _{D(ON)}	—	30.7	—	ns	V _{GS} = -4.5V, V _{DS} = -30V, R _G = 50Ω, I _D = -10mA
Turn-On Rise Time	t _R	—	84.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	201.8	—		
Turn-Off Fall Time	t _F	—	32.2	—		

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 7. Repetitive rating, pulse width limited by junction temperature.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.



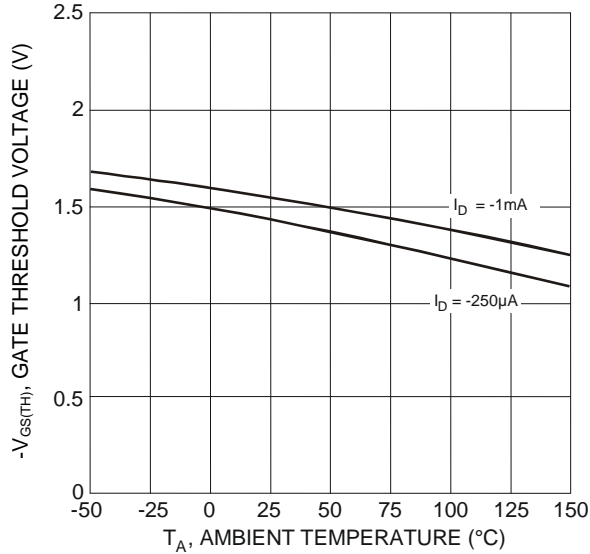


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

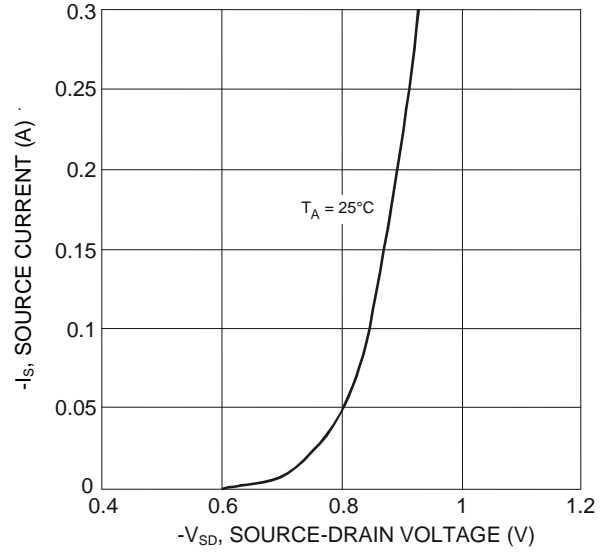


Fig. 8 Diode Forward Voltage vs. Current

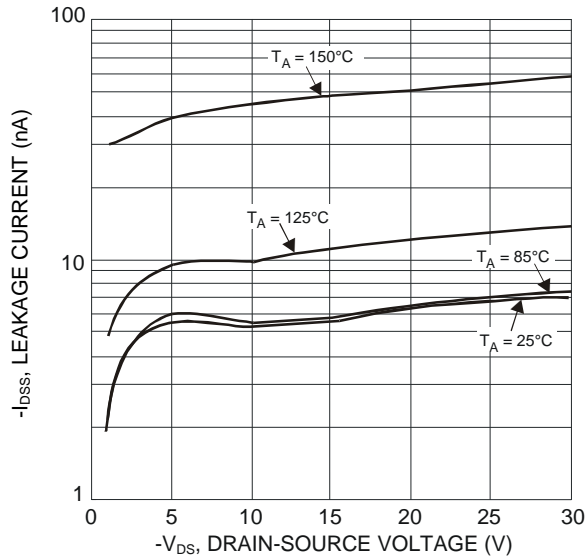


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

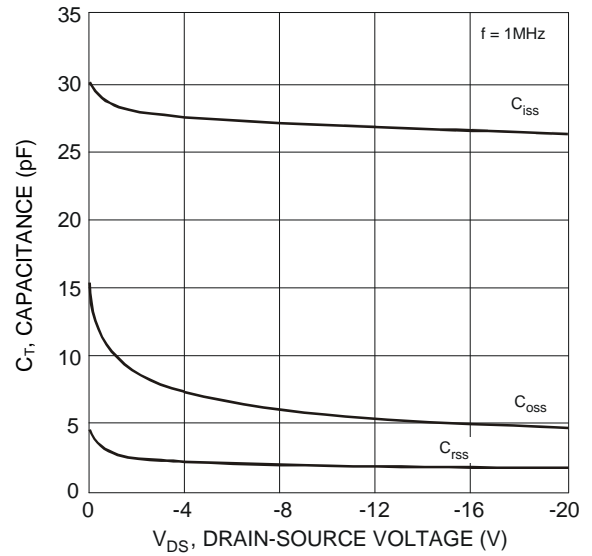


Fig. 10 Typical Junction Capacitance

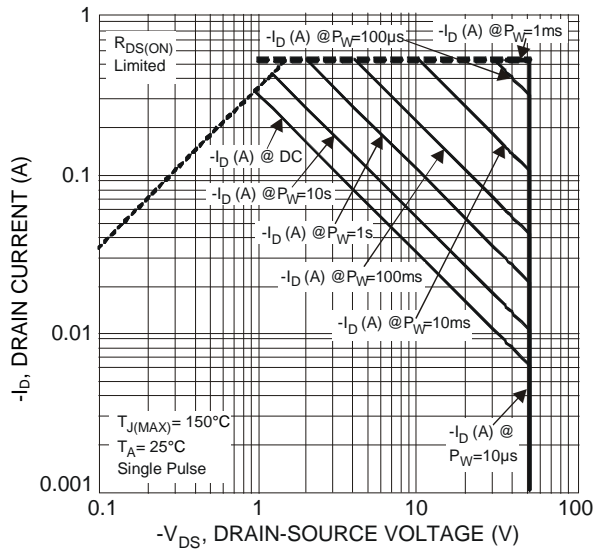
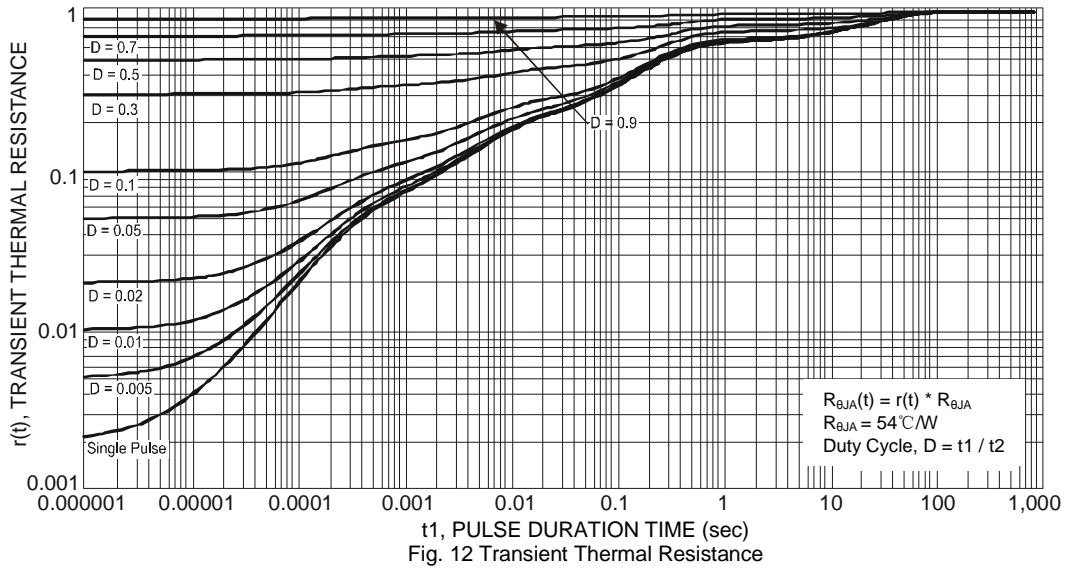


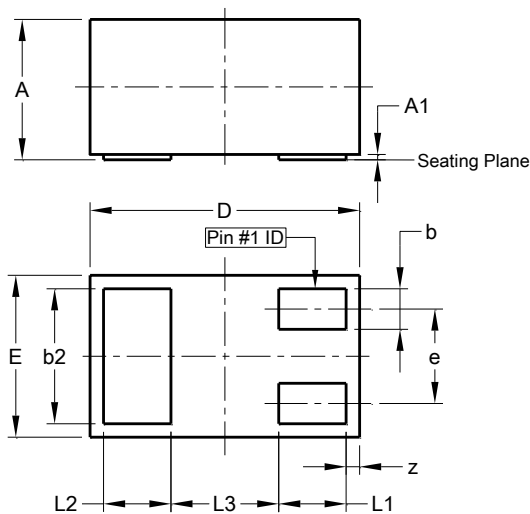
Fig. 11 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3



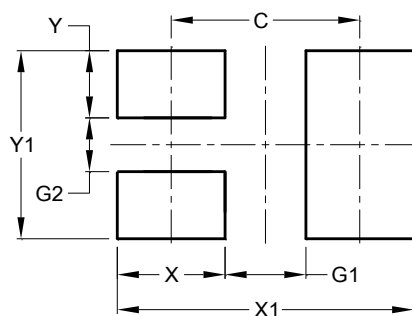
X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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